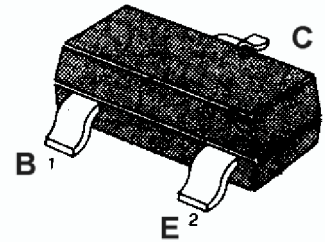


APPLICATION: High Voltage Amplifier Applications.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-300	V
Collector-emitter voltage	V _{CE0}	-300	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-500	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23


1.Base 2 .Emitter 3 .Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE1}	40				V _{CE} = -10V, I _C = -10mA
	h _{FE2}	25				V _{CE} = -10V, I _C = -30mA
Collector Cut-off Current	I _{CB0}			-0.25	μA	V _{CB} = -200V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -3V, I _C =0
Collector-Base Breakdown Voltage	BV _{CB0}	-300			V	I _C = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CE0}	-300			V	I _C = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.5	V	I _C = -20mA, I _B = -2mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			-0.9	V	I _C = -20mA, I _B = -2mA
Gain bandwidth product	f _T	50			MHz	I _C = -20mA, V _{CE} = -10V
Common Base Output Capacitance	C _{ob}			6	PF	V _{CB} = -20V, I _E =0, f=1MHz

h_{FE} Classification And Marking

Print Mark	YYV
Classification	
h _{FE1}	>40